



ALPHA & OMEGA
SEMICONDUCTOR



AO9926E

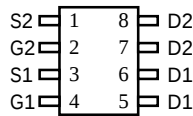
Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

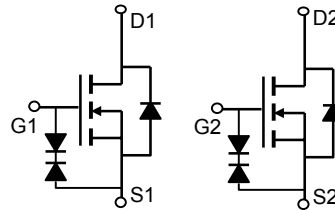
The AO9926E uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. *Standard Product AO9926E is Pb-free (meets ROHS & Sony 259 specifications). AO9926EL is a Green Product ordering option. AO9926E and AO9926EL are*

Features

V_{DS} (V) = 20V
 I_D = 8A (V_{GS} = 4.5V)
 $R_{DS(ON)} < 21m\Omega$ (V_{GS} = 4.5V)
 $R_{DS(ON)} < 25m\Omega$ (V_{GS} = 2.5V)
 $R_{DS(ON)} < 33m\Omega$ (V_{GS} = 1.8V)
 ESD Rating: 2000V HBM



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^A	I_D	8	A
	I_D	6.4	A
Pulsed Drain Current ^B	I_{DM}	30	A
Power Dissipation ^A	P_D	2	W
	P_D	1.28	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	74	110	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	35	40	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±4.5V			±1	μA
		V _{DS} =0V, V _{GS} =±8V			±10	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	0.4	0.6	1	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.5V, I _D =8A T _J =125°C		18 25	21 30	mΩ
		V _{GS} =2.5V, I _D =7A		21	25	mΩ
		V _{GS} =1.8V, I _D =6A		25	33	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =8A		29		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.76	1	V
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz		1160		pF
C _{oss}	Output Capacitance			187		pF
C _{rss}	Reverse Transfer Capacitance			146		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.5		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =8A		16		nC
Q _{gs}	Gate Source Charge			0.8		nC
Q _{gd}	Gate Drain Charge			3.8		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =5V, V _{DS} =10V, R _L =1.25Ω, R _{GEN} =3Ω		6.2		ns
t _r	Turn-On Rise Time			12.7		ns
t _{D(off)}	Turn-Off DelayTime			51.7		ns
t _f	Turn-Off Fall Time			16		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =8A, dI/dt=100A/μs		17.8		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =8A, dI/dt=100A/μs		6.8		nC

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev2: August 2005

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

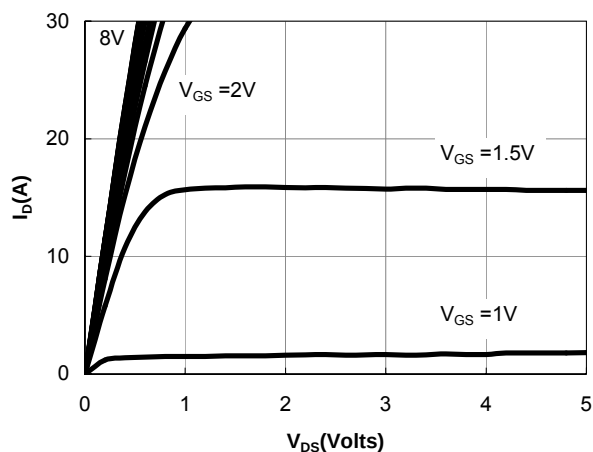


Figure 1: On-Regions Characteristics

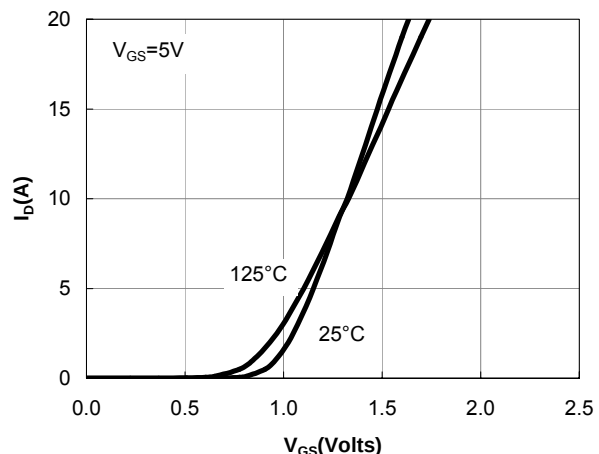


Figure 2: Transfer Characteristics

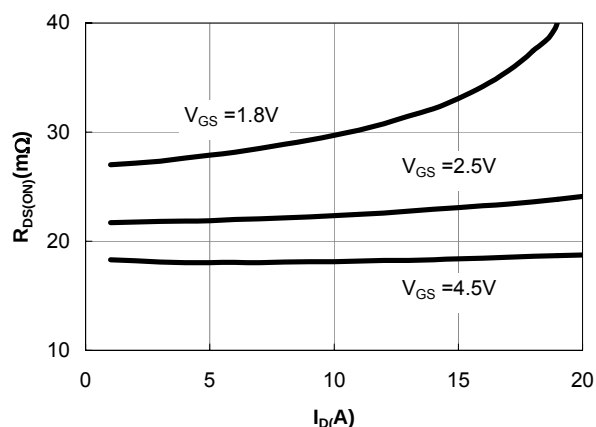


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

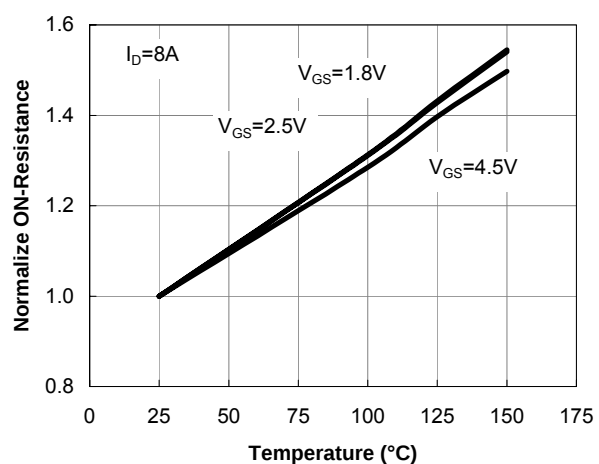


Figure 4: On-Resistance vs. Junction Temperature

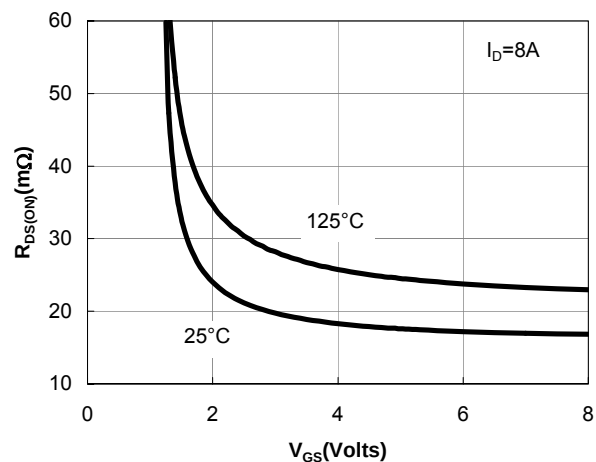


Figure 5: On-Resistance vs. Gate-Source Voltage

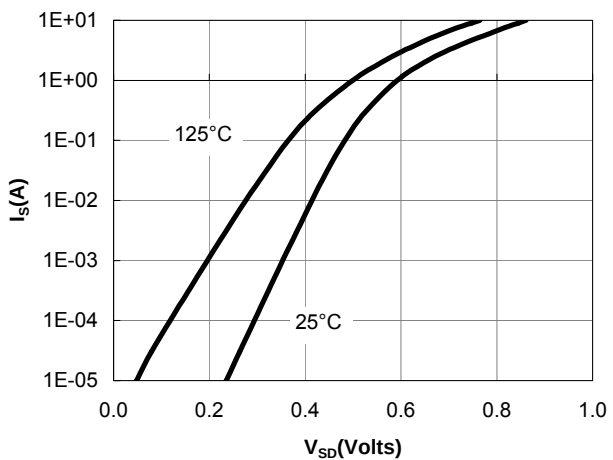


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

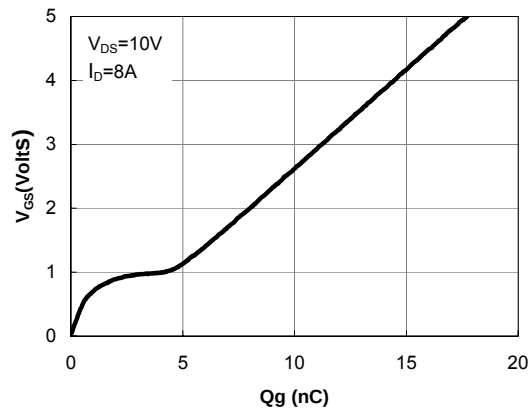


Figure 7: Gate-Charge Characteristics

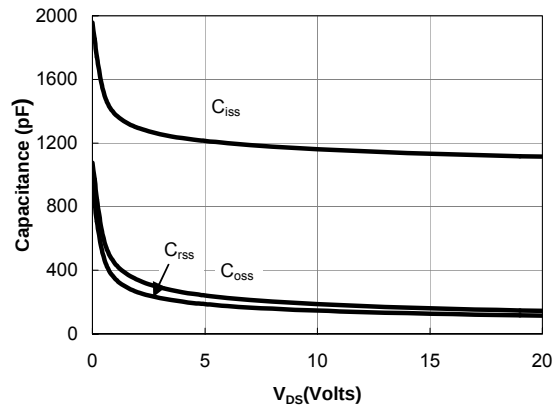


Figure 8: Capacitance Characteristics

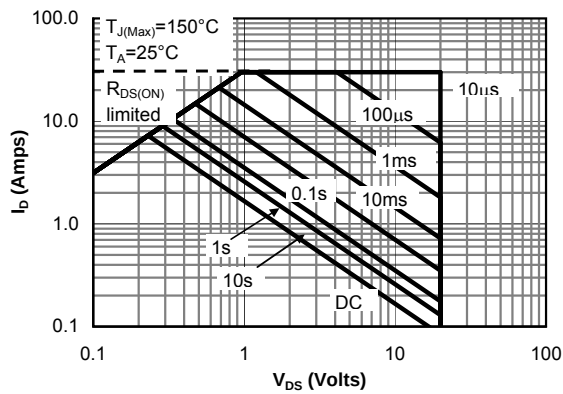


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

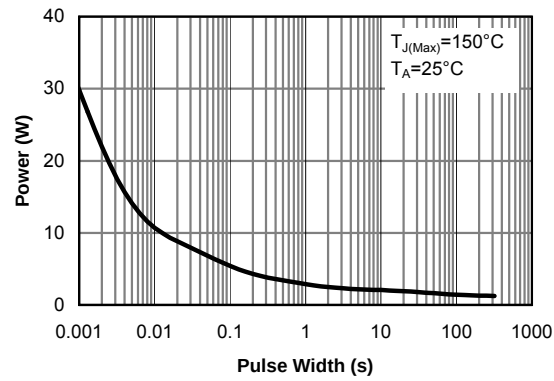


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

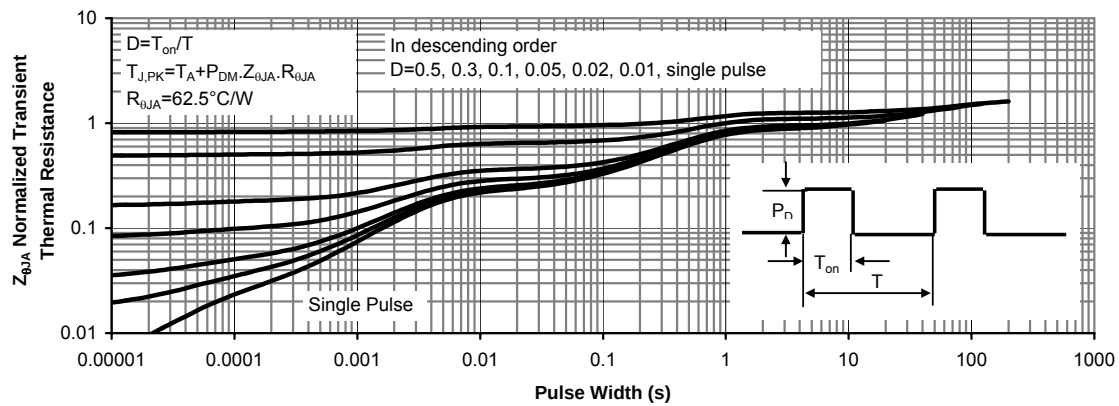


Figure 11: Normalized Maximum Transient Thermal Impedance